

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	234	control\$4 with conductivity with "metal oxide"	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L2	1981517	@ad> "20021011" or @rlad> "20021011"	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L3	131	L1 not L2	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L4	117535	DRAM	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L5	367078	capacitor	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L6	181980	electrode with substrate	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L7	1726333	@ad> "20030507" or @rlad> "20030507"	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L8	10823	L4 and L5 and L6	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L9	6898	L8 not L7	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L10	47181	electrode with (rear or opposite or backside or bottom or back) with substrate	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L11	1711	L9 and L10	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L12	4340	"trench capacitor"	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L13	273	L11 and L12	US-PGPUB; USPAT	OR	OFF	2008/08/30 11:59
L14	273	(438/608,609).CCLS.	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:02
L15	168	14 not 2	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:02
L16	19255	FET and ((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO)	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:03
L17	8	15 and 16	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:03
L18	19079	partial\$2 with pressure with oxygen	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:03
L19	0	17 and 18	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:03

L20	2960	FET and ((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/30 12:07
L21	7294	partial\$2 with pressure with oxygen	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/30 12:07
L22	2	20 and 21	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/30 12:07
L23	700	(257/E33.064,E31.126). OCLS.	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:11
L24	361	23 not 2	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:11
L25	23	18 and 24	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:11
L26	35176	critical with pressure	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:13
L27	0	25 and 26	US-PGPUB; USPAT	OR	OFF	2008/08/30 12:13
S1	1	("4204217").PN.	US-PGPUB; USPAT	OR	OFF	2007/06/08 12:46
S2	281309	(oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO	US-PGPUB; USPAT	OR	OFF	2007/06/08 12:57
S3	8351	((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO) with (PVD or "physical vapor" or "resistive evaporation" or "laser evaporaiton" or "electron beam evaporation" or CVD or "chemical vapor")	US-PGPUB; USPAT	OR	OFF	2007/06/08 12:58
S4	1402154	@ad> "20021011" or @rlad> "20021011"	US-PGPUB; USPAT	OR	OFF	2007/06/08 12:59
S5	5027	S3 not S4	US-PGPUB; USPAT	OR	OFF	2007/06/08 12:59
S6	16726	partial with pressure with oxygen	US-PGPUB; USPAT	OR	OFF	2007/06/08 13:00
S7	125	S5 and S6	US-PGPUB; USPAT	OR	OFF	2007/06/08 13:00
S8	99039	DRAM	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:35

S9	330169	capacitor	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:35
S10	155628	electrode with substrate	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:38
S11	5402960	@ad> "200"	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:36
S12	1171194	@ad> "20030507" or @rlad> "20030507"	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:36
S13	9695	S8 and S9 and S10	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:38
S14	6862	S13 not S12	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:38
S15	39962	electrode with (rear or opposite or backside or bottom or back) with substrate	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:48
S16	1704	S14 and S15	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:41
S17	3906	"trench capacitor"	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:41
S18	271	S16 and S17	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:41
S19	2149309	electrode near (rear or opposite or backside or bottom or back) near\$3 substrate	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:51
S20	24010	S8 and S9 and S19	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:50
S22	1780	electrode near (rear or opposite or backside or bottom or back) near substrate	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:51
S23	136	S8 and S9 and S22	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:51
S24	96	S23 not S12	US-PGPUB; USPAT	OR	OFF	2007/06/19 15:51
S25	12	("3791862"   "3850687"   "3852120"   "3925107"   "4176206"   "4784975").PN. OR ("5360768").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/19 16:03
S26	1	10/839,800	US-PGPUB; USPAT; USOCR	OR	OFF	2007/06/19 16:03
S27	1	("20030171080").PN.	US-PGPUB; USPAT	OR	OFF	2007/06/21 14:26
S28	1	("6440186").PN.	US-PGPUB; USPAT	OR	OFF	2007/06/21 14:26
S29	1	("6440186").PN.	US-PGPUB; USPAT	OR	OFF	2007/06/21 14:27

S30	297302	(oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO	US-PGPUB; USPAT	OR	OFF	2007/11/19 14:51
S31	1606905	@ad> "20021011" or @rlad> "20021011"	US-PGPUB; USPAT	OR	OFF	2007/11/19 14:51
S32	17852	((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO) with (FET or "field effect transistor")	US-PGPUB; USPAT	OR	OFF	2007/11/19 14:53
S33	3986	(deposit\$3 or form\$3) with ((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO) with (FET or "field effect transistor")	US-PGPUB; USPAT	OR	OFF	2007/11/19 14:54
S34	16	(deposit\$3 or form\$3) with ((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO) with transparent with (FET or "field effect transistor")	US-PGPUB; USPAT	OR	OFF	2007/11/19 14:54
S35	7	S34 not S31	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:05
S36	132874	ITO with PVD or CVD	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:05
S37	909	ITO with (PVD or CVD )	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:05
S38	1606905	@ad> "20021011" or @rlad> "20021011"	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:05
S39	523	S37 not S38	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:06
S40	0	ITO with (PVD or CVD ) with (FET or "field effect transistor")	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:06
S41	28	ITO with (PVD or CVD ) and (FET or "field effect transistor")	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:06
S42	14	S41 not S38	US-PGPUB; USPAT	OR	OFF	2007/11/19 17:06

S43	884	((oxide with semiconductor) or "zinc oxide" or ZnO or "indium oxide" or InO or "tin oxide" or SnO or "cadmium oxide" or CdO) with (PVD or "physical vapor" or "resistive evaporation" or "laser evaporation" or "electron beam evaporation" or CVD or "chemical vapor") with pressure	US-PGPUB; USPAT	OR	OFF	2008/06/19 12:00
S44	1889061	@ad> "20021011" or @rlad> "20021011"	US-PGPUB; USPAT	OR	OFF	2008/06/19 12:00
S45	533	S43 not S44	US-PGPUB; USPAT	OR	OFF	2008/06/19 12:14
S46	4	control\$4 with conductivity with "undoped metal oxide"	US-PGPUB; USPAT	OR	OFF	2008/06/19 12:15
S47	0	S46 not S44	US-PGPUB; USPAT	OR	OFF	2008/06/19 12:15
S48	229	control\$4 with conductivity with "metal oxide"	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:11
S49	1889061	@ad> "20021011" or @rlad> "20021011"	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:11
S50	131	S48 not S49	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:11
S51	4	control\$4 with conductivity with "metal oxide" with pressure	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:12
S52	0	S51 not S49	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:12
S53	1	("20030129424").PN.	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:21
S54	1	("20030129424").PN.	US-PGPUB; USPAT	OR	OFF	2008/06/19 14:23

8/30/08 12:28:58 PM

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